# MA3D650 (MA6D50)

# Silicon planar type (cathode common)

### For high-frequency rectification

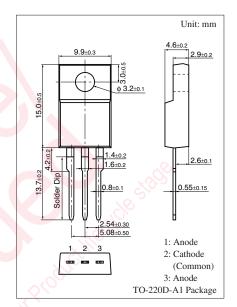
#### ■ Features

- Low forward voltage V<sub>F</sub>
- Fast reverse recovery time t<sub>rr</sub>
- TO-220D (Full-pack package) with high dielectric breakdown voltage
- Easy-to-mount, caused by its V cut lead end

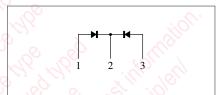
## ■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter                                   | Symbol             | Rating      | Unit |
|---|--------------------|-------------|------|
| Repetitive peak reverse voltage             | $V_{RRM}$          | 200         | V    |
| Non-repetitive peak reverse surge voltage   | V <sub>RSM</sub>   | 200         | V    |
| Forward current (Average)                   | I <sub>F(AV)</sub> | 10          | A    |
| Non-repetitive peak forward surge current * | $I_{FSM}$          | 60          | A    |
| Junction temperature                        | T <sub>j</sub>     | -40 to +150 | °C 0 |
| Storage temperature                         | $T_{stg}$          | -40 to +150 | °C   |

Note) \*: 50 Hz sine wave 1 cycle (Non-repetitive peak current)



#### Internal Connection

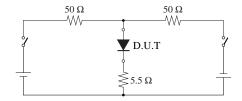


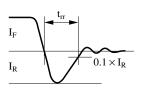
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

| Parameter                       | Symbol               | Conditions   | Min | Тур | Max  | Unit |
|---------------------------------|----------------------|--|-----|-----|------|------|
| Forward voltage                 | $V_{\rm F}$          | $I_F = 5 \text{ A}, T_C = 25^{\circ}\text{C}$        | .01 |     | 0.98 | V    |
| Repetitive peak reverse current | $I_{RRM1}$           | $V_{RRM} = 200 \text{ V}, T_C = 25^{\circ}\text{C}$  | 0.7 |     | 100  | μΑ   |
| - CO/V                          | I <sub>RRM2</sub>    | $V_{RRM} = 200 \text{ V}, T_j = 150^{\circ}\text{C}$ |     |     | 6    | mA   |
| Reverse recovery time *         | t <sub>rr</sub>      | $I_F = 1 A, I_R = 1 A$                               |     |     | 30   | ns   |
| Thermal resistance (j-c)        | R <sub>th(j-c)</sub> |  |     |     | 3.0  | °C/W |
| Thermal resistance (j-a)        | R <sub>th(j-a)</sub> | ils Wha  |     |     | 63   | °C/W |

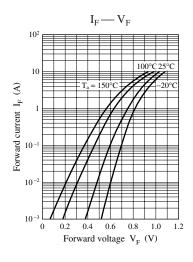
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

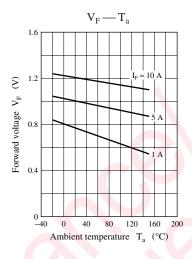
- 2. Absolute frequency of input and output is 10 MHz.
- 3. \*: t<sub>rr</sub> measurement circuit

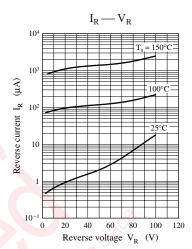


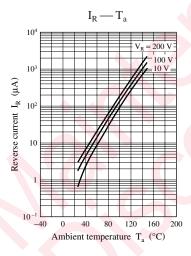


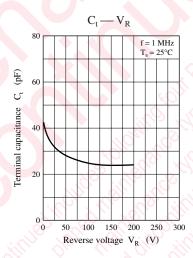
Note) The part number in the parenthesis shows conventional part number.

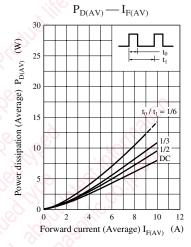


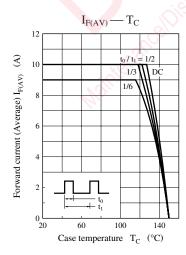












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